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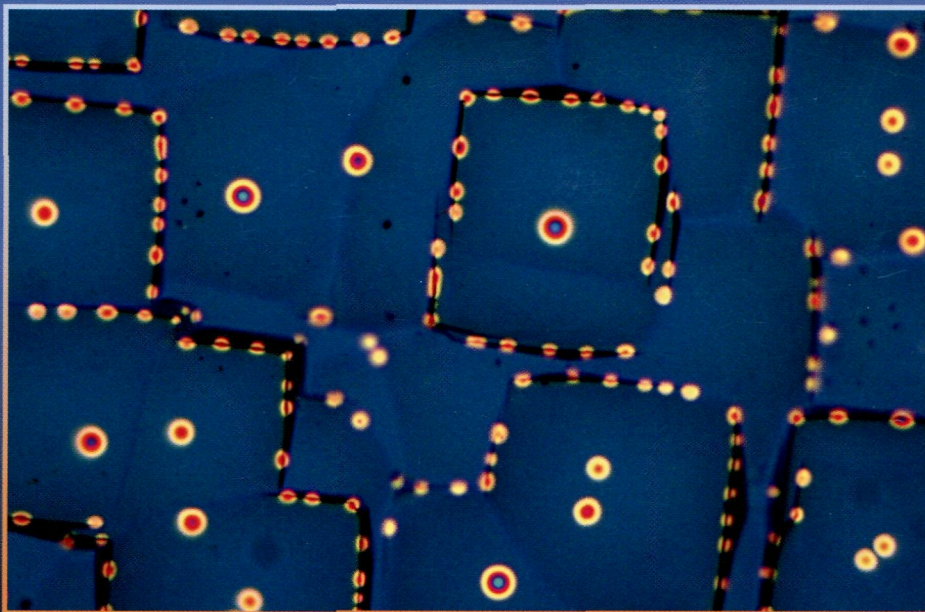


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Special Issue on Atomic Layer Deposition

Review Articles:

In situ Synchrotron Based X-ray Techniques as Monitoring Tools
for Atomic Layer Deposition

-by Kilian Devloo-Casier, Karl F. Ludwig, Christophe Detavernier and Jolien Dendooven

Reactor Concepts for Atomic Layer Deposition on Agitated Particles: A Review

-by Delphine Longrie, Davy Deduytsche and Christophe Detavernier



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On The Cover: *Front Credit: Stefan Bordihn, Verena Mertens, Jörg W. Müller, and W. M. M. (Erwin) Kessels, JVST A, 32(1), p. 01A128-5 (2014). Cover shows an optical microscopy image of a Czochralski silicon wafer passivated by an Al₂O₃/SiN_x film stack. The colorful circles are so-called “blisters” where the film stack has delaminated from the surface caused by hydrogen evolution from the Al₂O₃ film in a high temperature step.*